

N-channel 80 V, 5.1 mΩ standard level MOSFET in D2PAK Rev. 1 — 20 March 2012 Product data of

Product data sheet

#### **Product profile** 1.

#### **1.1 General description**

Standard level N-channel MOSFET in SOT404 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

#### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

#### **1.3 Applications**

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

#### 1.4 Quick reference data

Table 1.	Quick reference data						
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	80	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; see <u>Figure 1</u>	<u>[1]</u>	-	-	100	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	-	270	W
Tj	junction temperature			-55	-	175	°C
Static cha	aracteristics						
$R_{DSon}$	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 100 °C; see <u>Figure 13</u> ; see <u>Figure 12</u>		-	7.19	8.5	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 25 °C; see <u>Figure 12</u>		-	4.36	5.1	mΩ
Dynamic	characteristics						
Q <sub>GD</sub>	gate-drain charge	$V_{GS}$ = 10 V; $I_{D}$ = 25 A; $V_{DS}$ = 40 V;		-	21	-	nC
Q <sub>G(tot)</sub>	total gate charge	see Figure 14; see Figure 15		-	101	-	nC
Avalanch	e ruggedness						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \ \text{V}; \ T_{j(\text{init})} = 25 \ ^{\circ}\text{C}; \\ I_{D} = 100 \ \text{A}; \ V_{sup} \leq 80 \ \text{V}; \ R_{GS} = 50 \ \Omega; \\ \text{unclamped} \end{array}$		-	-	396	mJ

[1] Continuous current is limited by package

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#### N-channel 80 V, 5.1 mΩ standard level MOSFET in D2PAK

#### 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain <sup>[1]</sup>	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

[1] It is not possible to make connection to pin 2

#### 3. Ordering information

# Table 3. Ordering information Type number Package Name Description Version PSMN5R0-80BS D2PAK plastic single-ended surface-mounted package (D2PAK); 3 leads SOT404 (one lead cropped)

#### 4. Marking

Table 4. Marking codes	
Type number	Marking code
PSMN5R0-80BS	PSMN5R0-80BS

N-channel 80 V, 5.1 mΩ standard level MOSFET in D2PAK

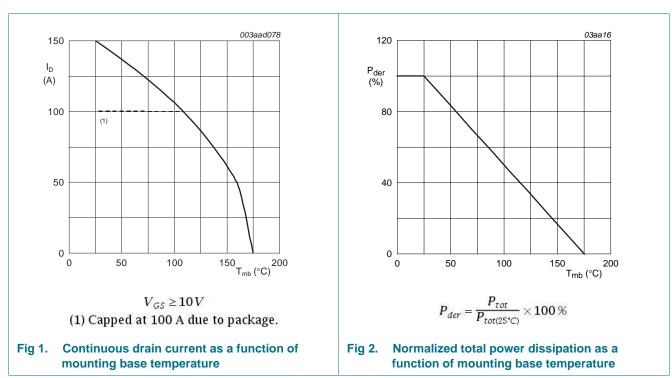
#### 5. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	80	V
V <sub>DGR</sub>	drain-gate voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C; R <sub>GS</sub> = 20 kΩ		-	80	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; see <u>Figure 1</u>	<u>[1]</u>	-	100	А
		$V_{GS}$ = 10 V; $T_{mb}$ = 25 °C; see <u>Figure 1</u>	<u>[1]</u>	-	100	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$ ; see Figure 3		-	598	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	270	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C
Source-dra	ain diode					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	-	100	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	598	А
Avalanche	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 100 A; $V_{sup} \le 80$ V; $R_{GS}$ = 50 $\Omega$ ; unclamped		-	396	mJ

[1] Continuous current is limited by package



## **PSMN5R0-80BS**

#### N-channel 80 V, 5.1 mΩ standard level MOSFET in D2PAK

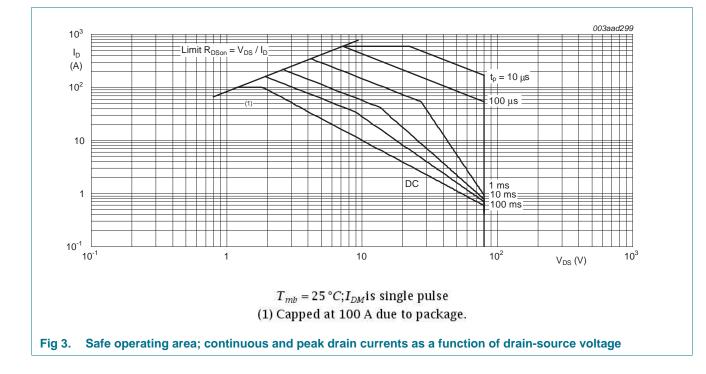


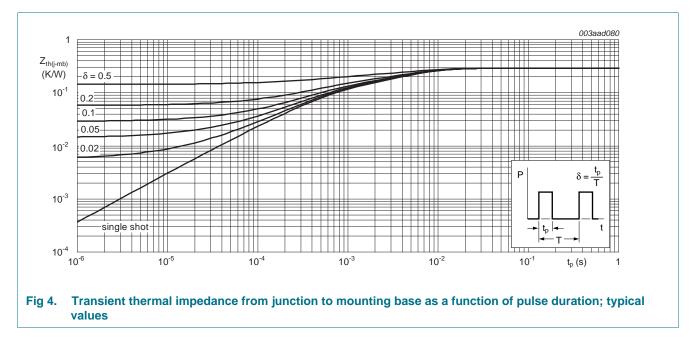
Table C

#### N-channel 80 V, 5.1 m $\Omega$ standard level MOSFET in D2PAK

#### 6. Thermal characteristics

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Table 6.	I nermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	see Figure 4	-	0.3	0.56	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	50	-	K/W



N-channel 80 V, 5.1 m $\Omega$  standard level MOSFET in D2PAK

#### 7. Characteristics

#### Table 7. Characteristics

Tested to JEDEC standards where applicable.

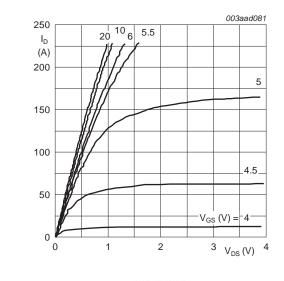
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V(BR)DSS drain-source breakdown voltage		$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ C$	73	-	-	V
		$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ C$	80	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see <u>Figure 10</u>	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see Figure 10	-	-	4.6	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 11</u> ; see <u>Figure 10</u>	2	3	4	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	8	μA
		$V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	150	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	10	100	nA
		$V_{GS} = 20 \text{ V};  V_{DS} = 0 \text{ V};  T_j = 25 ^{\circ}\text{C}$	-	10	100	nA
R <sub>DSon</sub> o	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ °C};$ see Figure 12; see Figure 13	-	10.46	12.3	Ω
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 \text{ °C};$ see Figure 13; see Figure 12	-	7.19	8.5	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 25 °C; see <u>Figure 12</u>	-	4.36	5.1	mΩ
R <sub>G</sub>	internal gate resistance (AC)	f = 1 MHz	-	0.95	-	Ω
Dynamic cl	haracteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 0 \text{ A}; \text{ V}_{DS} = 0 \text{ V}; \text{ V}_{GS} = 10 \text{ V}$	-	87	-	nC
		$I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};$	-	101	-	nC
$Q_{GS}$	gate-source charge	see <u>Figure 14;</u> see <u>Figure 15</u>	-	26	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge		-	18	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge		-	8	-	nC
$Q_{GD}$	gate-drain charge		-	21	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	$I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; \text{ see } \frac{\text{Figure } 14}{\text{Figure } 15}$	-	4.2	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	6793	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 16</u>	-	913	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	350	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 40 \text{ V}; \text{ R}_{L} = 0.5 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	33	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 4.7 \ \Omega$	-	21	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	73	-	ns
t <sub>f</sub>	fall time		-	14	-	ns

#### N-channel 80 V, 5.1 m $\Omega$ standard level MOSFET in D2PAK

#### Table 7. Characteristics ...continued

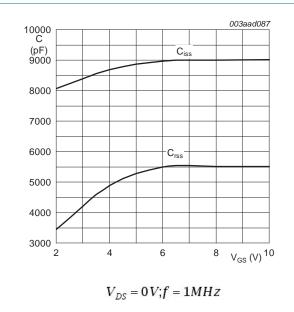
Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-drain diode						
$V_{SD}$	source-drain voltage	I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; see <u>Figure 17</u>	-	0.8	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{S} = 25 \text{ A}; \text{ d}I_{S}/\text{d}t = 100 \text{ A}/\mu\text{s};$	-	56	-	ns
Qr	recovered charge	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 40 V	-	116	-	nC

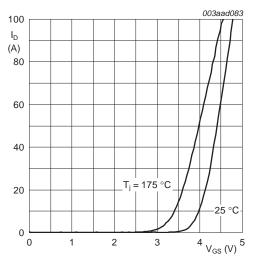


 $T_j = 25 \,^{\circ}C$ 



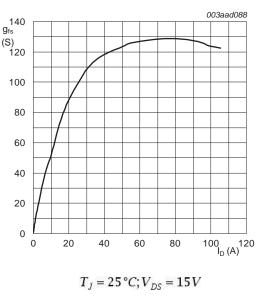






 $V_{DS} > I_D \times R_{DSon}$ 





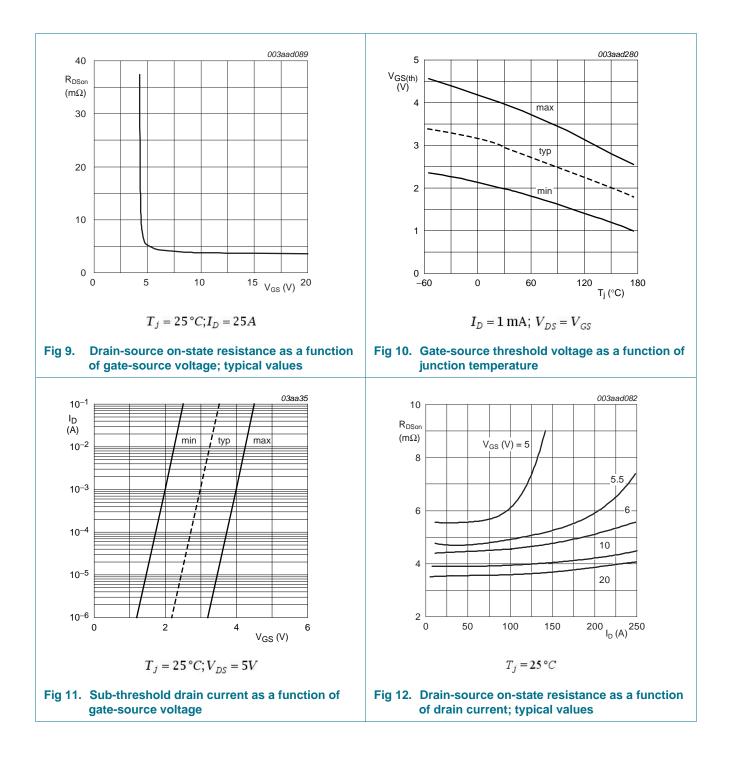


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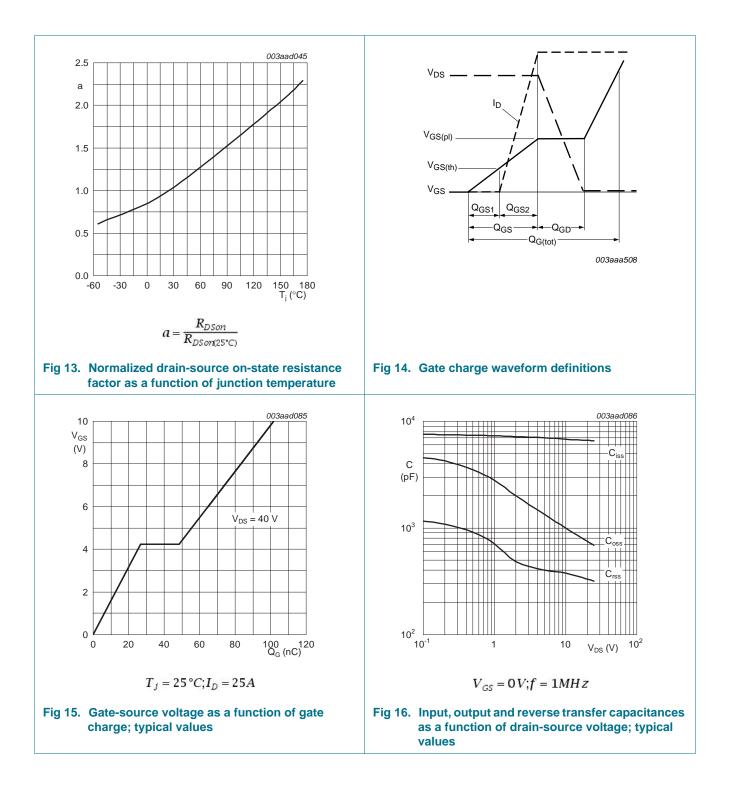
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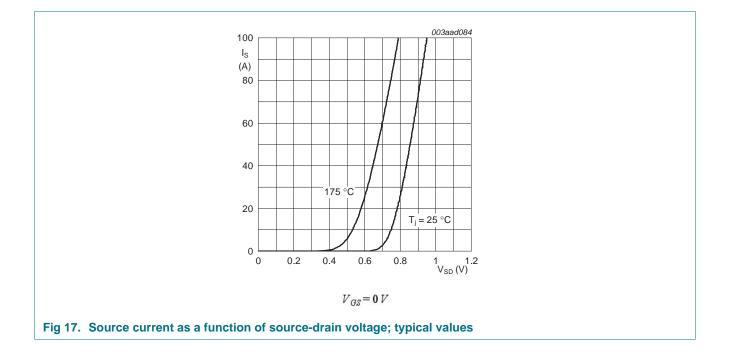
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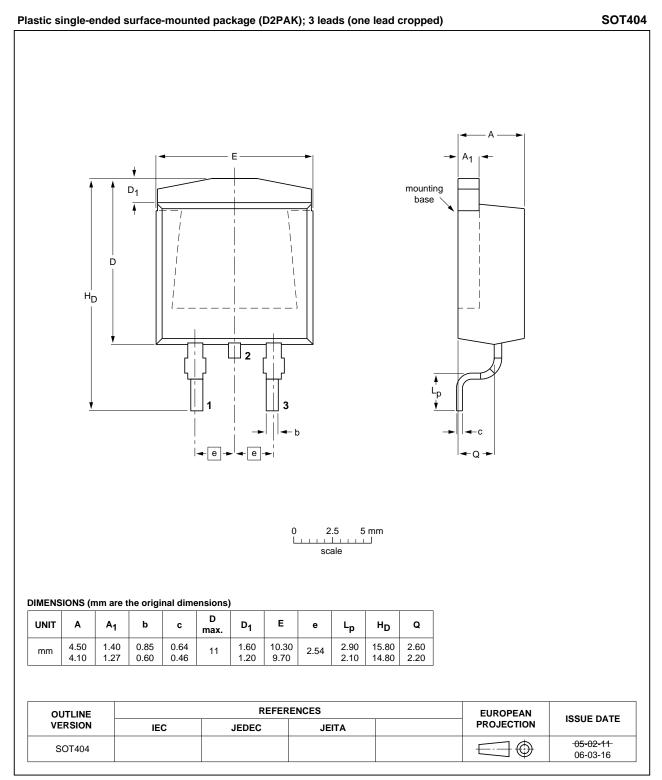
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#### N-channel 80 V, 5.1 m $\Omega$ standard level MOSFET in D2PAK



#### N-channel 80 V, 5.1 mΩ standard level MOSFET in D2PAK

#### 8. Package outline



#### Fig 18. Package outline SOT404 (D2PAK)

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#### N-channel 80 V, 5.1 mΩ standard level MOSFET in D2PAK

#### 9. Revision history

Table 8. Revision h	8. Revision history							
Document ID	Release date	Data sheet status	Change notice	Supersedes				
PSMN5R0-80BS v.1	20120320	Product data sheet	-	-				

#### **10. Legal information**

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Document status <sup>[1]</sup> [2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product data sheet

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